

AMENDMENTS TO THE CLAIMS:

Please cancel claims 1 and 2 without prejudice or disclaimer, and amend claims 3-5, 7, 8, 11 and 12, as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-2 (Canceled).

Claim 3 (Currently amended): A method of producing a semiconductor device ~~according to claim 1~~, comprising:

(1) epitaxially forming an electrically conducting thin film layer on a single crystalline substrate having through holes, epitaxially forming, on said electrically conducting thin film layer, ferroelectric single crystalline thin film containing Pb and having a plane (111) in parallel with the surface of the substrate, [[,]] patterning said electrically conducting thin film layer and said ferroelectric thin film layer to thereby form isolated ferroelectric thin films of a predetermined shape and one electrode of a capacitor of a predetermined shape, forming another electrode of the capacitor on said ferroelectric thin film, and forming part of a circuit of a semiconductor device so as to pass through the holes in said single crystalline substrate, to thereby fabricate a single crystalline substrate comprising a capacitor structure constituted by said ferroelectric thin film containing Pb and a pair of electrodes holding the ferroelectric thin film therebetween, and said part of the circuit of the semiconductor device;

(2) fabricating a semiconductor substrate having another circuit of the semiconductor device formed; and

(3) bonding said single crystalline substrate to said semiconductor substrate to couple the circuits of the two substrates together.

Claim 4 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein said ferroelectric material is PZT ($\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$), PLZT ($\text{Pb}_y\text{La}_{1-y}\text{Zr}_x\text{Ti}_{1-x}\text{O}_3$), PLCSZT ((Pb, La, Ca, Sr)(Zr, Ti) O_3) or a substance derived therefrom by adding Nb thereto.

Claim 5 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein as said single crystalline substrate, a single crystalline substrate having a plane (111) on which the ferroelectric thin film is to be formed, or a single crystalline substrate having an offset angle from the plane (111) is used.

Claim 6 (Original): A method of producing a semiconductor device according to claim 5, wherein said single crystalline substrate is an MgO or SrTiO_3 single crystalline substrate.

Claim 7 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein as said single crystalline substrate, an $\alpha\text{-Al}_2\text{O}_3$ single crystalline substrate having a plane (0001) on which the ferroelectric thin film is to be formed, or an $\alpha\text{-Al}_2\text{O}_3$ single crystalline substrate having an offset angle from the plane (0001), is used.

Claim 8 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein as said single crystalline substrate an MgAl_2O_4 single crystalline substrate having a plane (001) on which the ferroelectric thin film is to be formed, is used.

Claims 9-10 (Canceled).

Claim 11 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein as said single crystalline substrate a single crystalline silicon substrate having a plane {111} on which the ferroelectric thin film is to be formed or a single crystalline silicon substrate having an offset angle from the plane {111}, is used.

Claim 12 (Currently amended): A method of producing a semiconductor device according to claim [[1]] 3, wherein as said single crystalline substrate, a single crystalline silicon substrate having a plane {100} on which the ferroelectric thin film is to be formed, or a single crystalline silicon substrate having an offset angle from the plane {100}, is used.

Claim 13 (Previously Presented): A method of producing a semiconductor device according to claim 11, wherein said ferroelectric thin film is epitaxially grown directly on the ferroelectric thin film-forming surface of said single crystalline substrate.

Claim 14 (Previously Presented): A method of producing a semiconductor device according to claim 11, wherein said ferroelectric thin film is epitaxially grown through a buffer layer formed on the ferroelectric thin film-forming surface of said single crystalline substrate.

Claim 15 (Original): A method of producing a semiconductor device according to claim 14, wherein said buffer layer is formed of MgO, yttrium-stabilized zirconia, MgAl_2O_4 , CaO, SrTiO_3 or CeO_2 , and said ferroelectric thin film is grown on the plane (111) or the plane (0001) thereof.

Claims 16-23 (Canceled).